

I. Power section

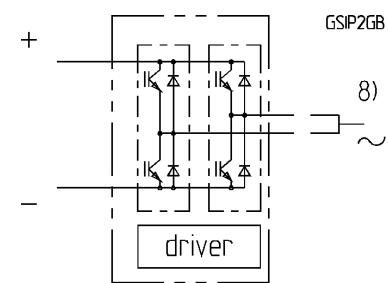
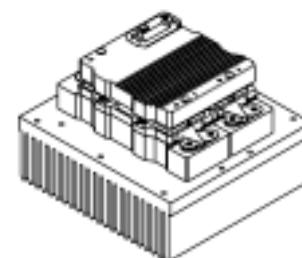
Absolute maximum ratings		$T_s = 25^\circ\text{C}$ unless otherwise specified		
Symbol	Conditions	Values	Units	
IGBT				
$V_{CES}^{(1)}$	Operating DC link voltage	1200 900 ± 20	V V V	
V_{GES}		1200 (900)	A	
I_c	$T_s = 25 \text{ (70) } ^\circ\text{C}$			
Inverse diode				
$I_F = -I_c$	$T_s = 25 \text{ (70) } ^\circ\text{C}$	900 (670)	A	
I_{FSM}	$T_j = 150 \text{ } ^\circ\text{C}, t_p = 10\text{ms}; \sin$	8640	A	
I^2t (Diode)	Diode, $T_i = 150 \text{ } ^\circ\text{C}, 10\text{ms}$	373	kA ² s	
$T_j, (T_{stg})$		-40...+150 (125)	°C	
V_{isol}	rms, AC, 1min per AC terminal, rms, $T_s = 70^\circ\text{C}$, $T_{terminal} < 115^\circ\text{C}$	3000 400	V A	
$ I_{AC\text{-terminal}}$				

Characteristics $T_s = 25^\circ\text{C}$ unless otherwise specified					
Symbol	Conditions	min.	typ.	max.	
IGBT					
V_{CEsat}	$I_c = 600\text{A}, T_j = 25 \text{ (125) } ^\circ\text{C};$ measured at terminal	-	1,7 (1,9)	2,1	V
V_{CEO}	$T_j = 25 \text{ (125) } ^\circ\text{C};$ at terminal	-	0,9 (0,8)	1,1 (1,0)	V
r_{CE}	$T_j = 25 \text{ (125) } ^\circ\text{C};$ at terminal	-	1,3 (1,8)	1,7 (2,2)	mΩ
I_{CES}	$V_{GE}=0, V_{CE}=V_{CES}, T_j=25(125) \text{ } ^\circ\text{C}$	-	2,4 (72)	-	mA
$E_{on} + E_{off}$	$I_c=600\text{A}, V_{cc}=600\text{V}$ $T_j=125^\circ\text{C}$	-	228	-	mJ
L_{CE}	top, bottom	-	6	-	nH
C_{CHC}	per phase, AC side	-	3,4	-	nF
$R_{CC\text{-EE}}$	terminal-chip, $T_j=25 \text{ } ^\circ\text{C}$	-	0,25	-	mΩ
Inverse diode					
$V_F = V_{EC}$	$I_F = 600\text{A}; T_j = 25(125) \text{ } ^\circ\text{C}$ measured at terminal	-	1,5 (1,5)	1,8	V
V_{TO}	$T_j = 25 \text{ (125) } ^\circ\text{C}$	-	0,9 (0,7)	1,1 (0,9)	V
r_T	$T_j = 25 \text{ (125) } ^\circ\text{C}$	-	1,0 (1,3)	1,1 (1,5)	mΩ
E_{RR}	$I_c=600\text{A}, V_{cc}=600\text{V}$ $T_j=125^\circ\text{C}$	-	42	-	mJ
-	$V_{cc}=900\text{V}$	-	56	-	mJ
Mechanical data					
M_{dc}	DC terminals, SI Units	6	-	8	Nm
M_{ac}	AC terminals, SI Units	13	-	15	Nm
w	SKiiP® 3 System w/o heat sink	-	1,7	-	kg
w	heat sink	-	5,4	-	kg
Thermal characteristics (PX16 heat sink with fan SKF16B-230-1); "s" reference to heat sink; "r" reference to built-in temperature sensor (acc. IEC 60747-15)					
$R_{thjsIGBT}$	per IGBT	-	-	0,030	°C/W
$R_{thjsdiode}$	per diode	-	-	0,058	°C/W
Z_{th}	$R_i (\text{mK/W})$ (max. values)		tau(s)		
	1 2 3 4	1	2	3	4
IGBT _{jr}	9,8 16,4 3,8 0,0	0,37	0,06	0,01	1,0
diode _{jr}	10,0 24,0 24,0 36,0	50,0	5,0	0,25	0,04
heatsink _{ra}	4,3 20,3 7,1 2,3	160	53	9,0	0,4

SKiiP® 3**SK integrated intelligent Power 2-pack****SKiiP 1213GB123-2DL**

Preliminary data

Case S23

**Features**

- SKiiP technology inside
- Trench IGBTs
- CAL HD diode technology
- integrated current sensor
- integrated temperature sensor
- integrated heat sink
- IEC 60721-3-3 (humidity) class 3K3/IE32 (SKiiP® 3 System)
- IEC 68T.1 (climate) 40/125/56 (SKiiP® 3 power section)
- UL recognized File no. E63532 (SKiiP® 3 power section)

- 1) with assembly of suitable MKP capacitor per terminal (SEMIKRON type is recommended)
- 8) AC connection busbars must be connected by the user; copper busbars available on request

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee, expressed or implied is made regarding delivery, performance or suitability.

SKiiP 1213GB123-2DL

SKiiP 3®

SK integrated intelligent Power

SKiiP 1213GB123-2DL

Preliminary data

II. Integrated gate driver

Absolute maximum ratings

Symbol	Term	Value	Unit
V_{S2}	Unstabilized 24V power supply	30	V
V_{iH}	Input signal voltage (high)	15 + 0,3	V
dv/dt	Secondary to primary side	75	kV/μs
V_{isoIO}	Input / output (AC, rms, 2 s)	3000	V
V_{isoPD}	Partial discharge extinction voltage, rms, $Q_{PD} \leq 10 \text{ pC}$;	1170	V
V_{isol12}	Output 1 / output 2 (AC, rms, 2s)	1500	V
f	Switching frequency	12	kHz
T_{op} (T_{stg})	Operating / storage temperature	- 40 ... + 85	°C

Gate driver features

- CMOS compatible inputs
- wide range power supply
- integrated circuitry to sense phase current, heat sink temperature and DC-bus voltage (option)
- short circuit protection
- over current protection
- over voltage protection (option)
- power supply protected against under voltage
- interlock of top/bottom switch
- isolation by transformers
- fibre optic interface (option for GB-types only)
- IEC 68T.1 (climate) 40/85/56 (SKiiP® 3 gate driver)

Electrical characteristics ($T_a = 25^\circ\text{C}$)

Symbol	Term	Values
		min typ max. Units
V_{S2}	Supply voltage non stabilized	13 24 27 V
I_{S2}	$V_{S2} = 24\text{V}$	$274 + 25*f / \text{kHz} + 0,00022 * (I_{AC}/A)^2$ mA
V_{IT+}	Input threshold voltage (High)	11,2 – – V
V_{IT-}	Input threshold voltage (Low)	– – 5,4 V
R_{in}	Input resistance	– 10 – kΩ
C_{in}	Input capacitance	– 1 – nF
$t_{d(on)IO}$	Input-output turn-on propagation time	– 1,1 – μs
$t_{d(off)IO}$	Input-output turn-off propagation time	– 1,1 – μs
$t_pERRRESET$	Error memory reset time	– 9 – μs
t_{TD}	top/bottom switch: interlock time	– 3,3 – μs
$I_{analogOUT}$	Max. 5mA ; 8 V corresponds to 15 V supply voltage for external components; max load current	– 1200 – A
I_{S1out}		– – 50 mA
I_{TRIPSC}	over current trip level ($I_{analog OUT} = 10\text{V}$)	– 1500 – A
T_{tp}	over temperature protection	110 – 120 °C
U_{DCTRIP}	U_{DC} -protection ($U_{analog OUT} = 9\text{V}$) (option for GB types)	not implemented – – V

For electrical and thermal design support please use SEMISEL. Access to SEMISEL is via SEMIKRON website <http://www.semikron.com>.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.